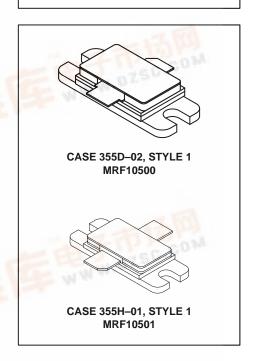
The RF Line Microwave Pulse Power Transistors

... designed for 1025–1150 MHz pulse common base amplifier applications such as TCAS, TACAN and Mode–S transmitters.

- Guaranteed Performance @ 1090 MHz
 Output Power = 500 Watts Peak
 Gain = 8.5 dB Min, 9.0 dB (Typ)
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Hermetically Sealed Industry Package
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- · Internal Input and Output Matching
- Characterized with 10 μs, 1% Duty Cycle Pulses

MRF10500 MRF10501

500 W (PEAK) 1025-1150 MHz MICROWAVE POWER TRANSISTORS NPN SILICON



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCES	65	Vdc
Collector-Base Voltage	Vcво	65	Vdc
Emitter-Base Voltage	VEBO	3.5	Vdc
Collector Current — Peak (1)	lC lC	29	Adc
Total Device Dissipation @ T _C = 25°C (1), (2) Derate above 25°C		1460 8.3	Watts W/°C
Storage Temperature Range		-65 to +200	°C
Junction Temperature	TJ	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)		0.12	°C/W

NOTES:

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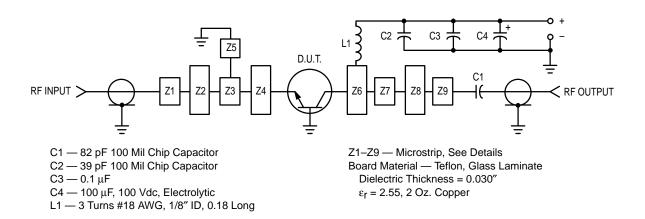
- 1. Under pulse RF operating conditions.
- 2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.

Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ_{JC} value measured @ 32 μ s, 2%.)



ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I _C = 60 mAdc, V _{BE} = 0)	V(BR)CES	65	_	_	Vdc
Collector–Base Breakdown Voltage (I _C = 60 mAdc, I _E = 0)	V(BR)CBO	65	_	_	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 mAdc, I _C = 0)	V(BR)EBO	3.5	_	_	Vdc
Collector Cutoff Current (V _{CB} = 36 Vdc, I _E = 0)	ICBO	_	_	25	mAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 5.0 Adc, V _{CE} = 5.0 Vdc)	hFE	20	_	_	_
FUNCTIONAL TESTS					
Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz)	G _{PB}	8.5	9.0	_	dB
Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz)	η	40	45	_	%
Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 500 W Peak, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	Ψ	No Degradation in Output Power			



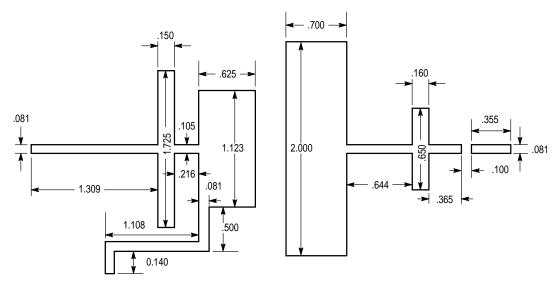


Figure 1. Test Circuit

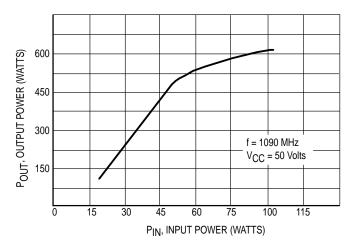
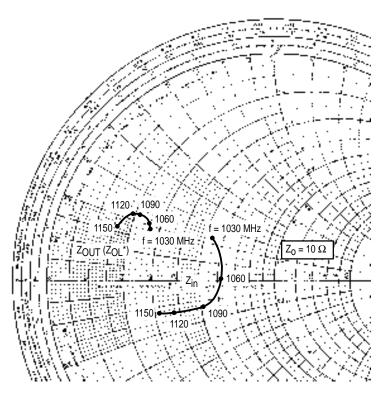


Figure 2. Output Power versus Input Power



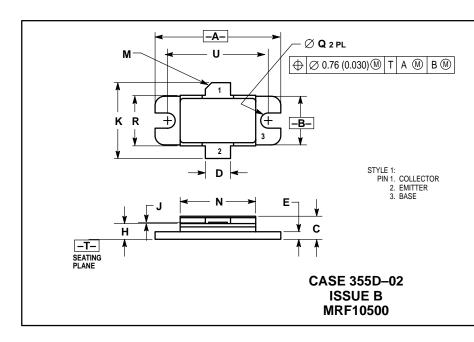
 $P_{OUT} = 500 \text{ W Pk} \quad V_{CC} = 50 \text{ V}$

f MHz	Z _{in} OHMS	Z _{OL} * (Z _{OUT}) OHMS
1030	5.3 + j2.25	2.6 + j1.89
1060	6.2 + j0.2	2.56 + j2.0
1090	5.2 – j1.4	2.12 + j2.2
1120	3.7 – j1.35	1.9 + j2.15
1150	3.15 – j1.3	1.6 + j1.62

 Z_{OL}^{\star} is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

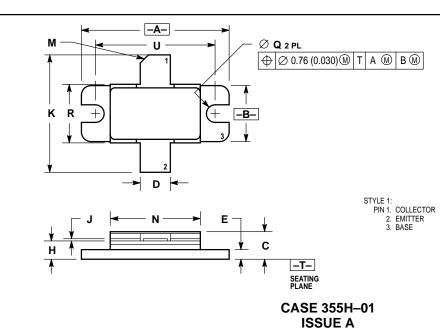
PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.990	1.010	25.15	25.65	
В	0.375	0.395	9.53	10.03	
O	0.150	0.165	3.81	4.19	
D	0.195	0.205	4.95	5.21	
Е	0.055	0.065	1.40	1.65	
Н	0.120	0.130	3.05	3.30	
Ĺ	0.003	0.006	0.08	0.15	
Κ	0.570	0.630	14.48	16.00	
М	45 °REF		45 °REF		
N	0.590	0.610	14.99	15.49	
Q	0.115	0.125	2.92	3.18	
R	0.395	0.405	10.03	10.29	
C	0.800 BSC 20.32 BSC		BSC		



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 VIA 5M 1082
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.990	1.010	25.15	25.65	
В	0.375	0.395	9.53	10.03	
С	0.150	0.165	3.81	4.19	
D	0.195	0.205	4.95	5.21	
Е	0.055	0.065	1.40	1.65	
Н	0.120	0.130	3.05	3.30	
J	0.003	0.006	0.08	0.15	
K	0.780	0.820	19.81	20.83	
М	45° REF		45°	REF	
N	0.590	0.610	14.99	15.49	
Q	0.115	0.125	2.92	3.18	
R	0.395	0.405	10.03	10.29	
U	0.800 BSC		20.32	BSC	

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